Semiconductors

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Diode Characteristics





C-V CHARACTERISTIC OF A STANDARD DIODE

Optical Setup for Carrier Dynamics





Lock In Amplifier





Max resolution =
$$\frac{1.22\lambda}{NA}$$

Our Ideal resolution 1.25 microns

Our Beam needs to be measured...

Image from last years group



I=Intrinsic region: pure semiconductor without doping



0 VOLT DEPLETION REGION MEASUREMENT

Approx. 40 **μm**



Approx. 45 **μm**





Deep Level Transient Spectroscopy (DLTS)

- Measures the electrically active defects in semiconductors (known as carrier traps).
 - Traps hold electrons or holes.
- 1. Steady state voltage is disturbed with a voltage pulse, causing carriers to be trapped.
- 2. After the pulse the trapped carriers can be emitted back to their steady state.
- 3. The total voltage decays back to 0 slower than the applied pulse.

DLTS Setup

Whole Overview





DLTS Circuit



Measurements





What We would expect

This pulse is with no diode attached. Without the diode we would expect no decaying curve and a fast rise and decay for the pulse in our circuit.

Measurements with Diodes

Standard Diode

Schottky Barrier Rectifier 1N5817

Fast Response Diode

P6KE





Stand Alone Component Set-up



DLTS vs. Stand Alone Components

DLTS



Stand Alone Components



Cryostat

• Mounted diodes in cryostat for liquid nitrogen temperature measurements





What's Next

- Verify spot size
 - Knife Edge measurement
- Explore band edge issues
 - Need a tunable Laser
- DLTS (Deep-Level Transient Spectroscopy)
 - Explore Pulse and Pulse response through system
 - Take measurements cooling the diodes through use of the Cyrostat
 - Consider using a Amplifier/Lock-in Amplifier and adding a capacitor to the end of the DLTS circuit